

Kosuke Nagashio

List of Publications by Year in descending order

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218
papers

5,520
citations

126907

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219
all docs

219
docs citations

219
times ranked

5958
citing authors

#	ARTICLE	IF	CITATIONS
1	Crystalline Graphdiyne Nanosheets Produced at a Gas/Liquid or Liquid/Liquid Interface. Journal of the American Chemical Society, 2017, 139, 3145-3152.	13.7	438
2	Contact resistivity and current flow path at metal/graphene contact. Applied Physics Letters, 2010, 97, .	3.3	282
3	Purely in-plane ferroelectricity in monolayer SnS at room temperature. Nature Communications, 2020, 11, 2428.	12.8	214
4	Uniform and ultrathin high- ϵ gate dielectrics for two-dimensional electronic devices. Nature Electronics, 2019, 2, 563-571.	26.0	204
5	Layer-by-Layer Dielectric Breakdown of Hexagonal Boron Nitride. ACS Nano, 2015, 9, 916-921.	14.6	174
6	Electrical transport properties of graphene on SiO ₂ with specific surface structures. Journal of Applied Physics, 2011, 110, .	2.5	167
7	Opportunities and challenges for Ge CMOS – Control of interfacing field on Ge is a key (Invited) Tj ETQq1 1 0.784314 rgBT /Overload	2.4	135
8	Mobility Variations in Mono- and Multi-Layer Graphene Films. Applied Physics Express, 0, 2, 025003.	2.4	131
9	High-Electron-Mobility Ge/GeO_2 n-MOSFETs With Two-Step Oxidation. IEEE Transactions on Electron Devices, 2011, 58, 1295-1301.	3.0	118
10	Fully dry PMMA transfer of graphene on <i>h</i> -BN using a heating/cooling system. 2D Materials, 2015, 2, 041002.	4.4	116
11	Growth mechanism of twin-related and twin-free facet Si dendrites. Acta Materialia, 2005, 53, 3021-3029.	7.9	115
12	Desorption kinetics of GeO from GeO ₂ /Ge structure. Journal of Applied Physics, 2010, 108, .	2.5	112
13	Ge/GeO_2 Interface Control with High-Pressure Oxidation for Improving Electrical Characteristics. Applied Physics Express, 0, 2, 071404.	2.4	103
14	Systematic Investigation of the Intrinsic Channel Properties and Contact Resistance of Monolayer and Multilayer Graphene Field-Effect Transistor. Japanese Journal of Applied Physics, 2010, 49, 051304.	1.5	100
15	Metal/graphene contact as a performance Killer of ultra-high mobility graphene analysis of intrinsic mobility and contact resistance. , 2009, , .		86
16	Density-of-States Limited Contact Resistance in Graphene Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 070108.	1.5	76
17	High-Electron-Mobility Ge n-Channel Metal-“Oxide” Semiconductor Field-Effect Transistors with High-Pressure Oxidized Y_2O_3 . Applied Physics Express, 2011, 4, 064201.	2.4	73
18	Ge MOSFETs performance: Impact of Ge interface passivation. , 2010, , .		63

#	ARTICLE	IF	CITATIONS
19	Hydrogen-Assisted Epitaxial Growth of Monolayer Tungsten Disulfide and Seamless Grain Stitching. Chemistry of Materials, 2018, 30, 403-411.	6.7	60
20	Expansion of the Graphdiyne Family: A Triphenylene-Cored Analogue. ACS Applied Materials & Interfaces, 2019, 11, 2730-2733.	8.0	58
21	Record-high electron mobility in Ge n-MOSFETs exceeding Si universality. , 2009, , .		57
22	Anisotropic Dielectric Breakdown Strength of Single Crystal Hexagonal Boron Nitride. ACS Applied Materials & Interfaces, 2016, 8, 27877-27884.	8.0	53
23	Impacts of oxygen passivation on poly-crystalline germanium thin film transistor. Thin Solid Films, 2014, 557, 334-337.	1.8	47
24	Density-of-States Limited Contact Resistance in Graphene Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 070108.	1.5	44
25	Self-passivated ultra-thin SnS layers <i>via</i> mechanical exfoliation and post-oxidation. Nanoscale, 2018, 10, 22474-22483.	5.6	42
26	2D Tunnel Field Effect Transistors (FETs) with a Stable Chargeâ€¢Transferâ€¢Type p⁺+</sup>â€¢WSe₂ Source. Advanced Electronic Materials, 2018, 4, 1800207.	5.1	41
27	Material potential and scalability challenges of germanium CMOS. , 2011, , .		40
28	Rapid solidification of Y3Al5O12 garnet from hypercooled melt. Acta Materialia, 2001, 49, 1947-1955.	7.9	39
29	Junctionless Ge p-Channel Metalâ€¢Oxideâ€¢Semiconductor Field-Effect Transistors Fabricated on Ultrathin Ge-on-Insulator Substrate. Applied Physics Express, 2011, 4, 031302.	2.4	39
30	Full Energy Spectra of Interface State Densities for <i>n</i>â€¢and <i>p</i>â€¢type MoS₂ Fieldâ€¢Effect Transistors. Advanced Functional Materials, 2019, 29, 1904465.	14.9	39
31	Microstructural control of NdBa2Cu3O7â€¢ superconducting oxide from highly undercooled melt by containerless processing. Journal of Crystal Growth, 1999, 200, 118-125.	1.5	38
32	Phase selection of peritectic phase in undercooled Nd-based superconducting oxides. Acta Materialia, 2000, 48, 3049-3057.	7.9	38
33	Metastable Phase Formation from an Undercooled Rare-Earth Orthoferrite Melt. Journal of the American Ceramic Society, 2002, 85, 2550-2556.	3.8	38
34	Gap state analysis in electric-field-induced band gap for bilayer graphene. Scientific Reports, 2015, 5, 15789.	3.3	36
35	Estimation of residual carrier density near the Dirac point in graphene through quantum capacitance measurement. Applied Physics Letters, 2013, 102, .	3.3	35
36	Characterization of electron mobility in ultrathin body germanium-on-insulator metal-insulator-semiconductor field-effect transistors. Applied Physics Letters, 2013, 102, .	3.3	35

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37	All 2D Heterostructure Tunnel Field-Effect Transistors: Impact of Band Alignment and Heterointerface Quality. ACS Applied Materials & Interfaces, 2020, 12, 51598-51606.	8.0	35
38	Microtexture and macrotexture formation in the containerless solidification of undercooled Ni ^{18.7} at.% Sn eutectic melts. Acta Materialia, 2005, 53, 731-741.	7.9	34
39	The density of states of graphene underneath a metal electrode and its correlation with the contact resistivity. Applied Physics Letters, 2013, 103, 033514.	3.3	34
40	Enhancement of thermal stability and water resistance in yttrium-doped GeO ₂ /Ge gate stack. Applied Physics Letters, 2014, 104, 092909.	3.3	34
41	Direct observation of charge transfer region at interfaces in graphene devices. Applied Physics Letters, 2013, 102, .	3.3	33
42	Structural and thermodynamic consideration of metal oxide doped GeO ₂ for gate stack formation on germanium. Journal of Applied Physics, 2014, 116, .	2.5	33
43	Pinpoint pick-up and bubble-free assembly of 2D materials using PDMS/PMMA polymers with lens shapes. Applied Physics Express, 2019, 12, 055008.	2.4	33
44	Density and Thermal Conductivity Measurements for Silicon Melt by Electromagnetic Levitation under a Static Magnetic Field. International Journal of Thermophysics, 2007, 28, 44-59.	2.1	32
45	Science of 2.5 dimensional materials: paradigm shift of materials science toward future social innovation. Science and Technology of Advanced Materials, 2022, 23, 275-299.	6.1	32
46	Direct observation of the crystal-growth transition in undercooled silicon. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2002, 33, 2947-2953.	2.2	30
47	Band tail interface states and quantum capacitance in a monolayer molybdenum disulfide field-effect-transistor. Journal Physics D: Applied Physics, 2018, 51, 065110.	2.8	30
48	Formation of Hexagonal Metastable Phases from an Undercooled LuFeO ₃ Melt in an Atmosphere with Low Oxygen Partial Pressure. Journal of the American Ceramic Society, 2008, 91, 806-812.	3.8	29
49	Conduction band offset at GeO ₂ /Ge interface determined by internal photoemission and charge-corrected x-ray photoelectron spectroscopies. Applied Physics Letters, 2013, 102, .	3.3	29
50	Low Temperature Phosphorus Activation in Germanium through Nickel Germanidation for Shallow n ⁺ /p Junction. Applied Physics Express, 0, 2, 021202.	2.4	28
51	Orbital-specific Tunability of Many-Body Effects in Bilayer Graphene by Gate Bias and Metal Contact. Scientific Reports, 2014, 4, 3713.	3.3	28
52	Accumulation-Mode Two-Dimensional Field-Effect Transistor: Operation Mechanism and Thickness Scaling Rule. ACS Applied Materials & Interfaces, 2018, 10, 32355-32364.	8.0	28
53	Isothermal Growth and Stacking Evolution in Highly Uniform Bernal-Stacked Bilayer Graphene. ACS Nano, 2020, 14, 6834-6844.	14.6	28
54	Spherical Yttrium Aluminum Garnet Embedded in a Glass Matrix. Journal of the American Ceramic Society, 2002, 85, 2353-2358.	3.8	27

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55	A comparative EBSD study of microstructure and microtexture formation from undercooled Ni99B1 melts solidified on an electrostatic levitator and an electromagnetic levitator. <i>Acta Materialia</i> , 2006, 54, 3791-3799.	7.9	26
56	Spherical Silicon Crystal Formed by Semisolid Process in Drop Tube. <i>Japanese Journal of Applied Physics</i> , 2006, 45, L623-L626.	1.5	26
57	Determination of Carrier Polarity in Fowlerâ€œNordheim Tunneling and Evidence of Fermi Level Pinning at the Hexagonal Boron Nitride/Metal Interface. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 11732-11738.	8.0	25
58	Phase selection in the undercooled peritectic Y3Fe5O12 melt. <i>Acta Materialia</i> , 2002, 50, 1973-1981.	7.9	24
59	In situ identification of the metastable phase during solidification from the undercooled YFeO3 melt by fast x-ray diffractometry at 250Hz. <i>Applied Physics Letters</i> , 2006, 89, 241923.	3.3	24
60	Ge/GeO2 Interface Control with High Pressure Oxidation for Improving Electrical Characteristics. <i>ECS Transactions</i> , 2009, 19, 165-173.	0.5	24
61	Oxygen potential engineering of interfacial layer for deep sub-nm EOT high-k gate stacks on Ge. , 2013, ,		24
62	Electrically Inert h-BN/Bilayer Graphene Interface in All-Two-Dimensional Heterostructure Field Effect Transistors. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 28780-28788.	8.0	24
63	Reexamination of the solidification behavior of undercooled Niâ€œSn eutectic melts. <i>Acta Materialia</i> , 2002, 50, 3241-3252.	7.9	23
64	Microstructure formation and in situ phase identification from undercooled Coâ€œ61.8at.% Si melts solidified on an electromagnetic levitator and an electrostatic levitator. <i>Acta Materialia</i> , 2008, 56, 2514-2525.	7.9	22
65	Hexagonal Boron Nitride As an Ideal Substrate for Carbon Nanotube Photonics. <i>ACS Photonics</i> , 2020, 7, 1773-1779.	6.6	22
66	Isotope Tracing Study of GeO Desorption Mechanism from GeO ₂ /Ge Stack Using ⁷³ Ge and ¹⁸ O. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DA01.	1.5	22
67	Micrometer-scale monolayer SnS growth by physical vapor deposition. <i>Nanoscale</i> , 2020, 12, 23274-23281.	5.6	21
68	Observation of Dipole Layer Formed at High- <i>k</i> /Dielectrics/SiO ₂ Interface with X-ray Photoelectron Spectroscopy. <i>Applied Physics Express</i> , 2010, 3, 061501.	2.4	19
69	Isotope Tracing Study of GeO Desorption Mechanism from GeO ₂ /Ge Stack Using ⁷³ Ge and ¹⁸ O. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 04DA01.	1.5	19
70	Fabrication and Surface Engineering of Two-Dimensional SnS Toward Piezoelectric Nanogenerator Application. <i>MRS Advances</i> , 2018, 3, 2809-2814.	0.9	19
71	Influence of interface dipole layers on the performance of graphene field effect transistors. <i>Carbon</i> , 2019, 152, 680-687.	10.3	19
72	On the origin of recalescence behaviors of undercooled single-phase mullite and double-phase Al ₂ O ₃ â€œZrO ₂ eutectic melts. <i>Scripta Materialia</i> , 2002, 47, 213-218.	5.2	18

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73	Spreading and solidification behavior of molten Si droplets impinging on substrates. <i>Acta Materialia</i> , 2004, 52, 5295-5301.	7.9	18
74	An investigation of the phase diagram of the Al–Ir binary system. <i>Intermetallics</i> , 2008, 16, 1171-1178.	3.9	18
75	(Invited) Oxidation, Diffusion and Desorption in a Ge/GeO ₂ System. <i>ECS Transactions</i> , 2010, 28, 171-180.	0.5	18
76	Experimental Demonstration of Higher-k Phase HfO ₂ Through Non-Equilibrium Thermal Treatment. <i>ECS Transactions</i> , 2010, 28, 203-212.	0.5	18
77	Large Fermi energy modulation in graphene transistors with high-pressure O ₂ -annealed Y ₂ O ₃ topgate insulators. <i>Applied Physics Letters</i> , 2014, 104, 083519.	3.3	18
78	Buffer layer engineering on graphene via various oxidation methods for atomic layer deposition. <i>Applied Physics Express</i> , 2016, 9, 125101.	2.4	18
79	Transport properties of the top and bottom surfaces in monolayer MoS ₂ grown by chemical vapor deposition. <i>Nanoscale</i> , 2017, 9, 13264-13271.	5.6	18
80	Grain Size Increase and Field-Effect Mobility Enhancement of Pentacene Thin Films Prepared in a Low-Pressure H ₂ Ambient. <i>Applied Physics Express</i> , 0, 1, 041801.	2.4	17
81	Control of Properties of GeO ₂ Films and Ge/GeO ₂ Interfaces by the Suppression of GeO Volatilization. <i>ECS Transactions</i> , 2009, 19, 101-116.	0.5	17
82	Carrier density modulation in graphene underneath Ni electrode. <i>Journal of Applied Physics</i> , 2013, 114, 024503.	2.5	17
83	Containerless solidification of highly undercooled Al ₂ O ₃ –ZrO ₂ eutectic melts on an aero-acoustic levitator. <i>Journal of Crystal Growth</i> , 2003, 249, 625-633.	1.5	16
84	Electron paramagnetic resonance of Cr ^[sup 2+] and Cr ^[sup 4+] ions in CdGeAs ₂ crystals. <i>Journal of Applied Physics</i> , 2003, 94, 7567.	2.5	16
85	Luminescence and optical absorption study of p-type CdGeAs ₂ . <i>Journal of Physics Condensed Matter</i> , 2004, 16, 1279-1286.	1.8	16
86	Correlation between dislocation etch pits and optical absorption in CdGeAs ₂ . <i>Journal of Crystal Growth</i> , 2004, 269, 195-206.	1.5	16
87	Novel criterion for formation of metastable phase from undercooled melt. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2007, 449-451, 675-679.	5.6	16
88	Experimental detection of active defects in few layers MoS ₂ through random telegraphic signals analysis observed in its FET characteristics. <i>2D Materials</i> , 2017, 4, 015035.	4.4	16
89	Material and Device Structure Designs for 2D Memory Devices Based on the Floating Gate Voltage Trajectory. <i>ACS Nano</i> , 2021, 15, 6658-6668.	14.6	16
90	Atomic-Step-Induced Screw-Dislocation-Driven Spiral Growth of SnS. <i>Chemistry of Materials</i> , 2021, 33, 186-194.	6.7	16

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91	Donor-acceptor pair emission near 0.55 eV in CdGeAs ₂ . Journal of Applied Physics, 2004, 95, 4840-4844.	2.5	15
92	Real-time x-ray observation of solidification from undercooled Si melt. Journal of Applied Physics, 2006, 100, 033524.	2.5	15
93	Comparison of device structures for the dielectric breakdown measurement of hexagonal boron nitride. Applied Physics Letters, 2016, 109, .	3.3	15
94	Impact ionization and transport properties of hexagonal boron nitride in a constant-voltage measurement. Physical Review B, 2018, 97, .	3.2	15
95	Experimental and Analytical Characterization of Dual-Gated Germanium Junctionless p-Channel Metal-Oxide-Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DA03.	1.5	15
96	Fragmentation of faceted dendrite in solidification of undercooled B-doped Si melts. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2005, 36, 3407-3413.	2.2	14
97	Experimental study of carrier transport in ultra-thin body GeOI MOSFETs. , 2011, , .		14
98	Effect of Si substrate on interfacial SiO ₂ scavenging in HfO ₂ /SiO ₂ /Si stacks. Applied Physics Letters, 2014, 105, .	3.3	14
99	Thermodynamics and Kinetics for Suppression of GeO Desorption by High Pressure Oxidation of Ge. Materials Research Society Symposia Proceedings, 2009, 1155, 1.	0.1	13
100	Counter Dipole Layer Formation in Multilayer High- κ Gate Stacks. Japanese Journal of Applied Physics, 2012, 51, 081303.	1.5	13
101	Atomic layer deposition of Y ₂ O ₃ on h-BN for a gate stack in graphene FETs. Nanotechnology, 2015, 26, 175708.	2.6	13
102	Kinetic Effects of O-Vacancy Generated by GeO ₂ /Ge Interfacial Reaction. Japanese Journal of Applied Physics, 2011, 50, 10PE04.	1.5	13
103	Direct growth of REBa ₂ Cu ₃ O _{7-δ} (RE=Yb, Er, Y, Dy, Eu, Sm, Nd and Pr) from undercooled melt using aero-acoustic levitator. Acta Materialia, 2001, 49, 2557-2565.	7.9	12
104	In situ observation of solidification behavior of Si melt dropped on Si wafer by IR thermography. Journal of Crystal Growth, 2005, 275, e1685-e1690.	1.5	12
105	Oxidation Rate Reduction of Ge with O ₂ Pressure Increase. Applied Physics Express, 2012, 5, 114001.	2.4	12
106	Thermally robust CMOS-aware Ge MOSFETs with high mobility at high-carrier densities on a single orientation Ge substrate. , 2014, , .		12
107	The crystal orientation relation and macroscopic surface roughness in hetero-epitaxial graphene grown on Cu/mica. Nanotechnology, 2014, 25, 185602.	2.6	12
108	Atomically flat planarization of Ge(100), (110), and (111) surfaces in H ₂ annealing. Applied Physics Express, 2014, 7, 051301.	2.4	12

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109	Subthreshold transport in mono- and multilayered MoS ₂ FETs. Applied Physics Express, 2015, 8, 065203.	2.4	12
110	Influence of Interlayer Stacking on Gate-Induced Carrier Accumulation in Bilayer MoS ₂ . ACS Applied Electronic Materials, 2020, 2, 1352-1357.	4.3	12
111	Containerless Solidification of Peritectic and Eutectic Ceramics Using Aero-Acoustic Levitator. Materials Science Forum, 2000, 329-330, 173-178.	0.3	11
112	Nucleation behaviour and anomalous eutectic formation in highly undercooled Fe ₂ O ₃ -La ₂ O ₃ eutectic melts. Philosophical Magazine, 2003, 83, 1095-1109.	1.6	11
113	Phase Selection in Undercooled Y ₃ Al ₅ O ₁₂ Melt. Materials Transactions, 2004, 45, 2723-2727.	1.2	11
114	Experimental evidence of crystal fragmentation from highly undercooled Ni ₉₉ B ₁ melts processed on an electrostatic levitator. Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science, 2005, 36, 3254-3257.	2.2	11
115	Direct observation of electron capture and emission processes by the time domain charge pumping measurement of MoS ₂ FET. Applied Physics Letters, 2018, 113, .	3.3	11
116	Understanding the Memory Window Overestimation of 2D Materials Based Floating Gate Type Memory Devices by Measuring Floating Gate Voltage. Small, 2020, 16, e2004907.	10.0	11
117	Quantitative Determination of Contradictory Bandgap Values of Bulk PdSe ₂ from Electrical Transport Properties. Advanced Functional Materials, 2022, 32, 2108061.	14.9	11
118	On occurrence of multiple-site crystallization in undercooled mullite melts. Scripta Materialia, 2001, 45, 1431-1437.	5.2	10
119	Formation of NdBa ₂ Cu ₃ O _{7-x} amorphous phase by combining aero-acoustic levitation and splat quenching. Journal of Materials Research, 2001, 16, 138-145.	2.6	10
120	Fiber growth of near stoichiometric LiNbO ₃ single crystals by the laser-heated pedestal growth method. Journal of Crystal Growth, 2004, 265, 190-197.	1.5	10
121	Containerless solidification of undercooled oxide and metallic eutectic melts. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2004, 375-377, 528-533.	5.6	10
122	Urbach rule used to explain the variation of the absorption edge in CdGeAs ₂ crystals. Journal of Physics Condensed Matter, 2005, 17, 549-558.	1.8	10
123	Experimental verification of ribbon formation process in chill-block melt spinning. Acta Materialia, 2006, 54, 2353-2360.	7.9	10
124	Comprehensive study of GeO ₂ ; oxidation, GeO desorption and GeO ₂ -metal interaction -understanding of Ge processing kinetics for perfect interface control-. , 2009, .		10
125	Interfacial Dipole at High- k Dielectric/SiO ₂ Interface: X-ray Photoelectron Spectroscopy Characteristics. Japanese Journal of Applied Physics, 2011, 50, 031502.	1.5	10
126	Step and Terrace Formation on Ge(111) Surface in H ₂ Annealing. Applied Physics Express, 2012, 5, 121301.	2.4	10

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127	Reconsideration of electron mobility in Ge n-MOSFETs from Ge substrate side — Atomically flat surface formation, layer-by-layer oxidation, and dissolved oxygen extraction. , 2013, , .		10
128	Thermodynamic Perspective on the Oxidation of Layered Materials and Surface Oxide Amelioration in 2D Devices. ACS Applied Materials & Interfaces, 2021, 13, 43282-43289.	8.0	10
129	Interfacial Dipole at High-kDielectric/SiO2Interface: X-ray Photoelectron Spectroscopy Characteristics. Japanese Journal of Applied Physics, 2011, 50, 031502.	1.5	10
130	Direct Crystallization of Y_{3}Fe_{5}O_{12} Garnet by Containerless Solidification Processing. Materials Transactions, 2001, 42, 233-237.	1.2	9
131	Formation of YxNd1âˆ™xBa2Cu3O7âˆ™Î (0âˆ™xâˆ™0.9) superconductors from an undercooled melt via aeroâ€acoustic levitation. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2003, 341, 1-8.	5.6	9
132	Spherical crystallization of Si during free fall in drop-tubes. Journal of Crystal Growth, 2009, 311, 722-726.	1.5	9
133	(Invited) Formation of Dipole Layers at Oxide Interfaces in High-k Gate Stacks. ECS Transactions, 2010, 33, 463-477.	0.5	9
134	Intrinsic graphene/metal contact. , 2012, , .		9
135	Carrier Distribution Control in van der Waals Heterostructures of S_{Mo}^{2} and WS_{2}^{2}	3.8	9
136	Containerless Solidification and Net Shaping by Splat Quenching of Undercooled Nd₂Fe₁₄B Melts. Materials Transactions, 2003, 44, 853-860.	1.2	8
137	Correlation of the electrical and optical properties of p-type CdGeAs2. Journal of Applied Physics, 2006, 99, 013512.	2.5	8
138	Dynamic process of dendrite fragmentation in solidification from undercooled Si melt using time-resolved x-ray diffraction. Applied Physics Letters, 2007, 91, 061916.	3.3	8
139	Study of Kinetic Behaviors of GeO in GeO2/Ge Stacks. ECS Transactions, 2008, 16, 187-194.	0.5	8
140	Electron mobility in high-k Ge-MISFETs goes up to higher. , 2010, , .		8
141	Molecularly-thin anatase field-effect transistors fabricated through the solid state transformation of titania nanosheets. Nanoscale, 2017, 9, 6471-6477.	5.6	8
142	Graphene field-effect transistor application-electric band structure of graphene in transistor structure extracted from quantum capacitance. Journal of Materials Research, 2017, 32, 64-72.	2.6	8
143	Understanding interface properties in 2D heterostructure FETs. Semiconductor Science and Technology, 2020, 35, 103003.	2.0	8
144	Intrinsic Electronic Transport Properties and Carrier Densities in PtS₂ and SnSe₂: Exploration of n⁺â€Source for 2D Tunnel FETs. Advanced Electronic Materials, 2021, 7, 2100292.	5.1	8

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145	Structural change in silicon from undercooled liquid state to crystalline state during crystallization. <i>Journal of Crystal Growth</i> , 2006, 294, 16-21.	1.5	7
146	Impacts of graphene/SiO ₂ interaction on FET mobility and Raman spectra in mechanically exfoliated graphene films. , 2010, , .		7
147	Recent Progress of Ge Technology for a Post-Si CMOS. <i>ECS Transactions</i> , 2011, 35, 443-456.	0.5	7
148	Experimental and Analytical Characterization of Dual-Gated Germanium Junctionless p-Channel Metal-Oxide Semiconductor Field-Effect Transistors. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 04DA03.	1.5	7
149	HfO ₂ -assisted SiO ₂ reduction in HfO ₂ /SiO ₂ /Si stacks. <i>Thin Solid Films</i> , 2014, 557, 272-275.	1.8	7
150	Reliability assessment of germanium gate stacks with promising initial characteristics. <i>Applied Physics Express</i> , 2015, 8, 021301.	2.4	7
151	Containerless solidification of highly undercooled mullite melts: Crystal growth behavior and microstructure formation. <i>Metallurgical and Materials Transactions A: Physical Metallurgy and Materials Science</i> , 2002, 33, 2677-2683.	2.2	6
152	Formation of Metastable Rare-Earth Iron Garnet by Splat Quenching. <i>Journal of the American Ceramic Society</i> , 2006, 89, 1504-1509.	3.8	6
153	Type-II HfS ₂ /MoS ₂ Heterojunction Transistors. <i>IEICE Transactions on Electronics</i> , 2018, E101.C, 338-342.	0.6	6
154	Quantum-mechanical effect in atomically thin MoS ₂ FET. <i>2D Materials</i> , 2020, 7, 014001.	4.4	6
155	Detection of both optical polarization and coherence transfers to excitonic valley states in CVD-grown monolayer MoS ₂ . <i>Applied Physics Express</i> , 2019, 12, 063005.	2.4	5
156	Microstructure formation and phase selection in the solidification of Al ₂ O ₃ -5 at% SiO ₂ melts by splat quenching. <i>Journal of Materials Research</i> , 2002, 17, 2026-2032.	2.6	4
157	In Situ Observation of Metastable Rare-Earth Iron Garnet Formed at the Melt/Substrate Interface by Splat Quenching. <i>Journal of the American Ceramic Society</i> , 2007, 90, 238-243.	3.8	4
158	Spreading and solidification of a highly undercooled Y ₃ Al ₅ O ₁₂ droplet impinging on a substrate. <i>International Journal of Heat and Mass Transfer</i> , 2008, 51, 2455-2461.	4.8	4
159	Resistive Switching Behaviors of NiO Bilayer Films with Different Crystallinity Layers. <i>ECS Transactions</i> , 2010, 28, 315-322.	0.5	4
160	Long range pinning interaction in ultra-thin insulator-inserted metal/germanium junctions. , 2010, , .		4
161	Kinetic Effects of O-Vacancy Generated by GeO ₂ /Ge Interfacial Reaction. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 10PE04.	1.5	4
162	Real-time x-ray diffraction of metastable phases during solidification from the undercooled LuFeO ₃ melt by two-dimensional detector at 1 kHz. <i>Applied Physics Letters</i> , 2012, 100, 191905.	3.3	4

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